ACTT10B-800CTN

Enhanced, high temperature ACTT power switch

Rev - 01 24 July 2017 Product data sheet

1. General description

AC Thyristor Triac power switch in a TO263 (D2PAK) surface mountable plastic package with self-protective clamping capabilities against low and high energy transients. This "series CTN" triac will commutate the full RMS current at the maximum rated junction temperature ($T_{j(max)}$ = 150 °C) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- High junction operating temperature capability ($T_{j(max)}$ = 150 °C)
- High minimum IGT for guaranteed immunity to gate noise
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Less sensitive gate for high noise immunity
- Surface mountable package
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt and IEC 61000-4-4 fast transient
- Package meets UL94V0 flammability requirement
- Package is RoHS compliant

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls
- Applications subject to high temperature ($T_{j(max)}$ = 150 °C)

4. Quick reference data

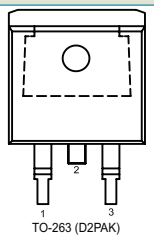
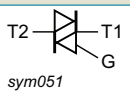
Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
Absolute maximum rating				
V_{DRM}	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	square-wave pulse; $T_{mb} \leq 126$ °C; Fig. 1; Fig. 2; Fig. 3	10	A
I_{TSM}	non-repetitive peak forward current	full sine wave; t_p = 20 ms; $T_{j(init)}$ = 25 °C; Fig. 4; Fig. 5	90	A
		full sine wave; t_p = 16.7 ms; $T_{j(init)}$ = 25 °C	99	A
T_j	junction temperature		150	°C

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+ T_j = 25 °C; Fig. 7		5	-	35	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G- T_j = 25 °C; Fig. 7		5	-	35	mA
		V_D = 12 V; I_T = 0.1 A; T2- G- T_j = 25 °C; Fig. 7		5	-	35	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	30	mA
V_T	on-state voltage	I_T = 14 A; T_j = 25 °C; Fig. 10		-	-	1.5	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		4000	-	-	V/µs
		V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		2000	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 10 A; dV_{com}/dt = 20 V/µs; gate open circuit; snubberless condition		5	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 10 A; dV_{com}/dt = 10 V/µs; gate open circuit		10	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 10 A; dV_{com}/dt = 1 V/µs; gate open circuit		15	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 TO-263 (D2PAK)	 sym051
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
ACTT10B-800CTN	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	TO-263

7. Marking

Table 4. Marking codes

Type number	Marking codes
ACTT10B-800CTN	ACTT10B-800CTN

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 126°C$; Fig. 1; Fig. 2; Fig. 3	10	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; t_p = 20 ms; $T_{j(init)}$ = 25 °C; Fig. 4; Fig. 5	90	A
		full sine wave; t_p = 16.7 ms; $T_{j(init)}$ = 25 °C	99	A
I^2t	I^2t for fusing	t_p = 10ms; sine wave	40	A^2/s
dI_T/dt	rate of rise of on-state current	I_G = 70mA	100	A/µs
I_{GM}	peak gate current		2	A
P_{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T_{stg}	storage temperature		-40 to 150	°C
T_j	junction temperature		150	°C
V_{pp}	peak pulse voltage	T_j = 25 °C; non-repetitive, off-state; ten pulses on each voltage polarity; 20s or more between successive pulses	2	kV

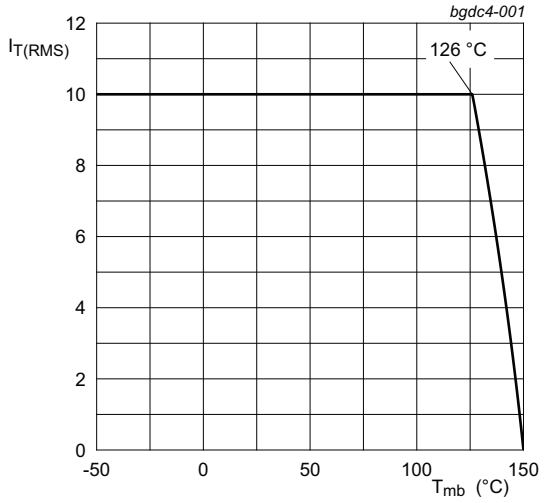
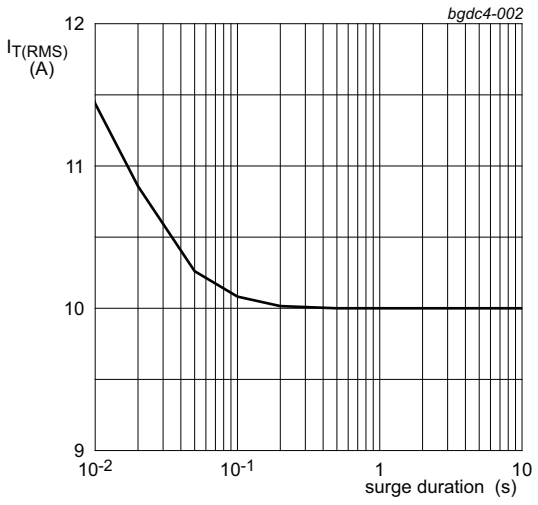
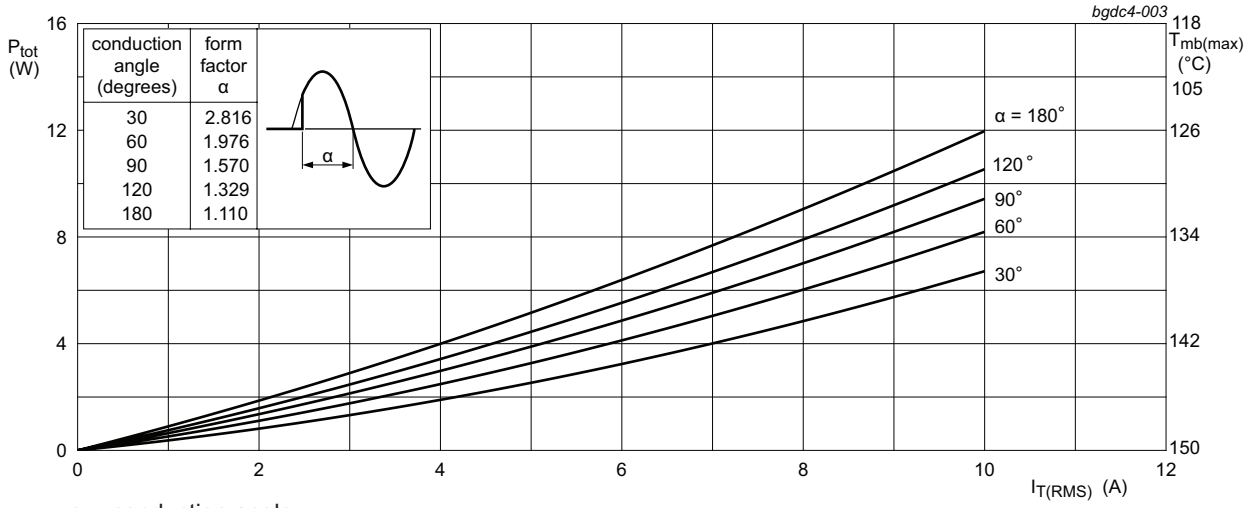


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50Hz; T_{mb} = 126 °C

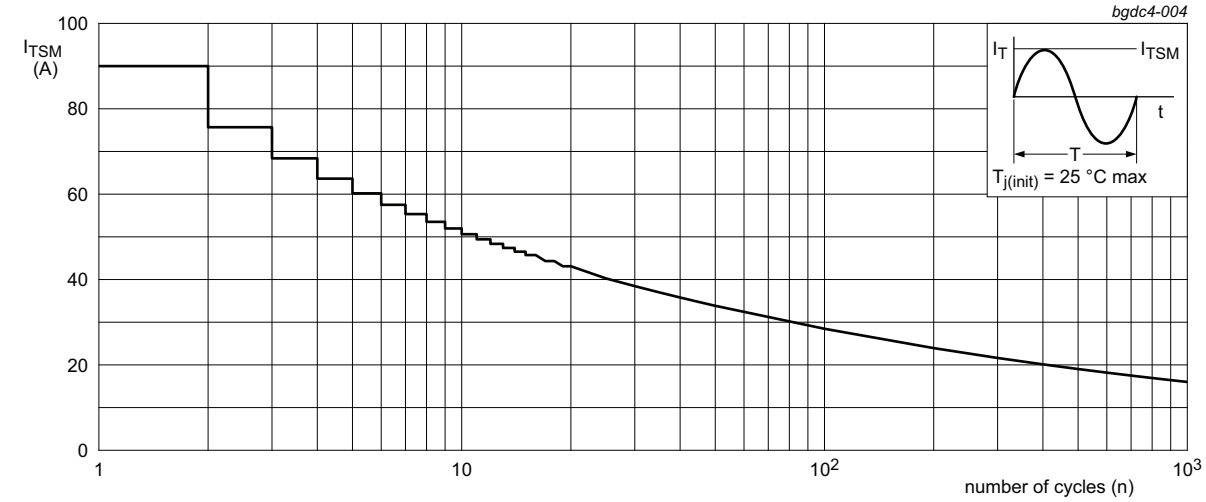
Fig. 2. RMS on-state current as a function of surge duration; maximum values



α = conduction angle

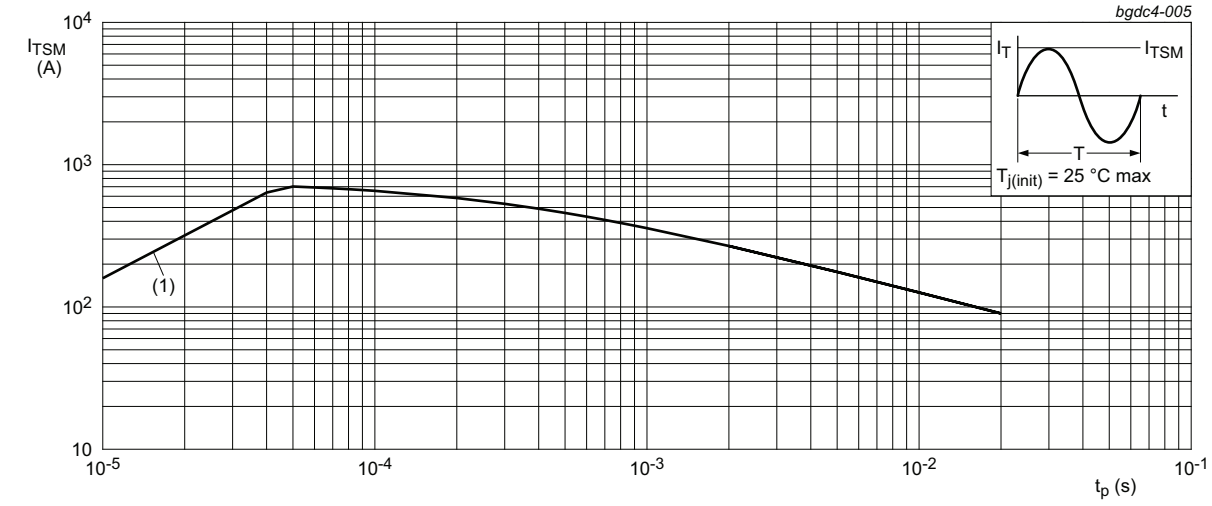
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



t_p ≤ 20 ms ;

(1) dI_T/dt limit

Fig. 5. Total power dissipation as a function of RMS on-state current; maximum values

9. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6		-	-	2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	55	-	K/W

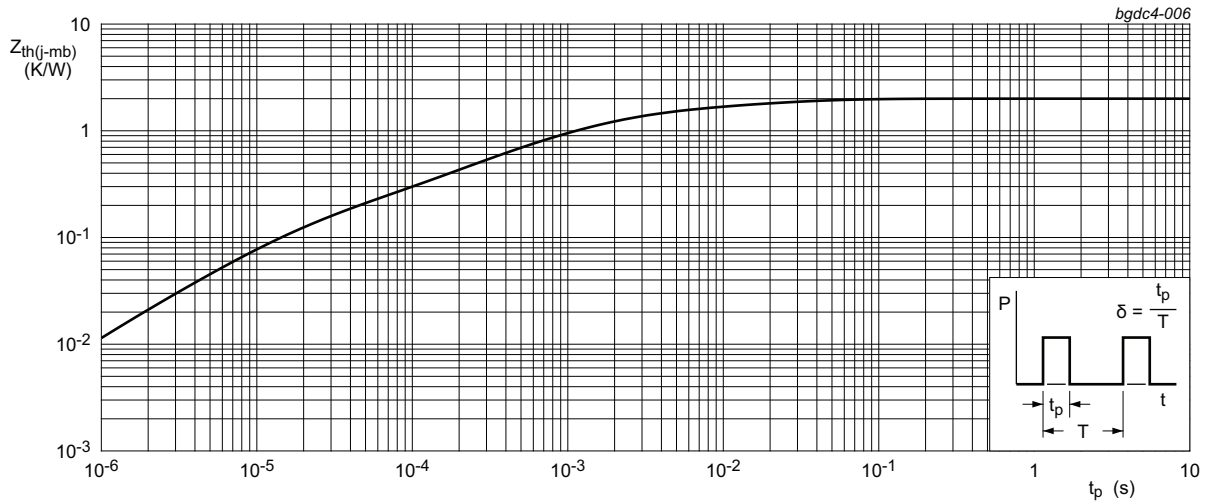
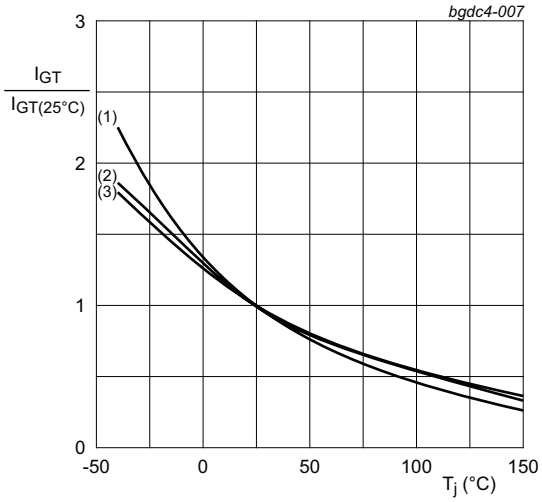


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 7		5	-	35	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 7		5	-	35	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 7		5	-	35	mA
I_L	latching current	V_D = 12 V; I_T = 0.1 A; T2+ G+; T_j = 25 °C; Fig. 8		-	-	40	mA
		V_D = 12 V; I_T = 0.1 A; T2+ G-; T_j = 25 °C; Fig. 8		-	-	50	mA
		V_D = 12 V; I_T = 0.1 A; T2- G-; T_j = 25 °C; Fig. 8		-	-	40	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	30	mA
V_T	on-state voltage	I_T = 14 A; T_j = 25 °C; Fig. 10		-	-	1.5	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 11		-	0.8	1	V
		V_D = 400 V; I_T = 0.1 A; T_j = 150 °C; Fig. 11		0.2	0.45	-	V
I_D	off-state current	V_D = 800 V; T_j = 25 °C		-	-	10	µA
		V_D = 800 V; T_j = 150 °C		-	-	2	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		4000	-	-	V/µs
		V_{DM} = 536 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		2000	-	-	V/µs
dI_{com}/dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 10 A; dV_{com}/dt = 20 V/µs; gate open circuit; snubberless condition		5	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 10 A; dV_{com}/dt = 10 V/µs; gate open circuit		10	-	-	A/ms
		V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 10 A; dV_{com}/dt = 10 V/µs; gate open circuit		15	-	-	A/ms



(1) T2- G-
(2) T2+ G-
(3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

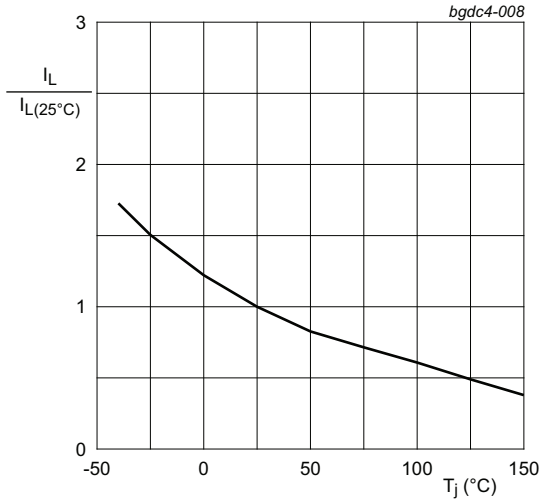


Fig. 8. Normalized latching current as a function of junction temperature

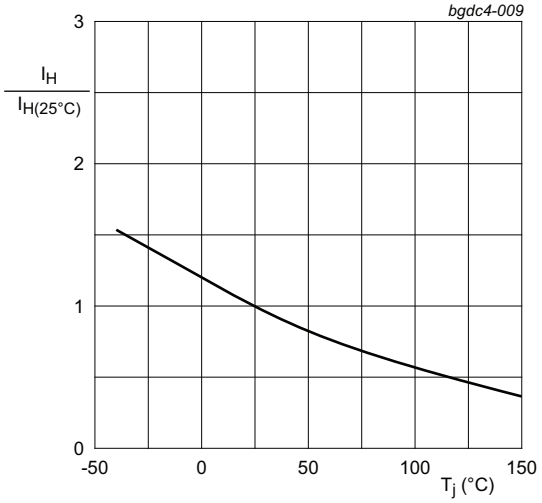
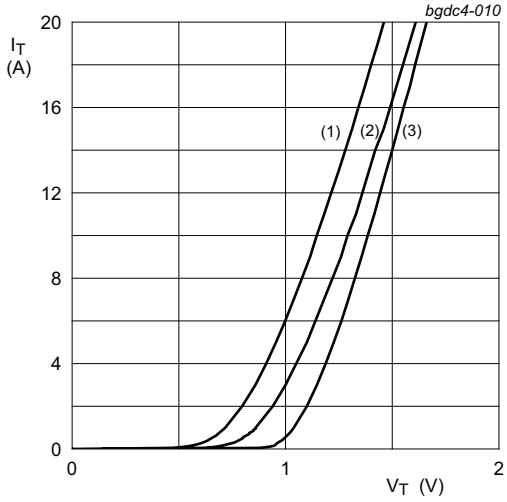


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 0.962 V; R_s = 0.0330 Ω
(1) T_j = 150 °C; typical values
(2) T_j = 150 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

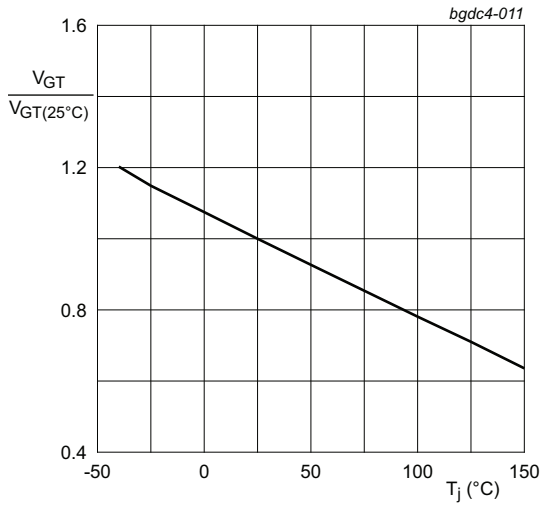
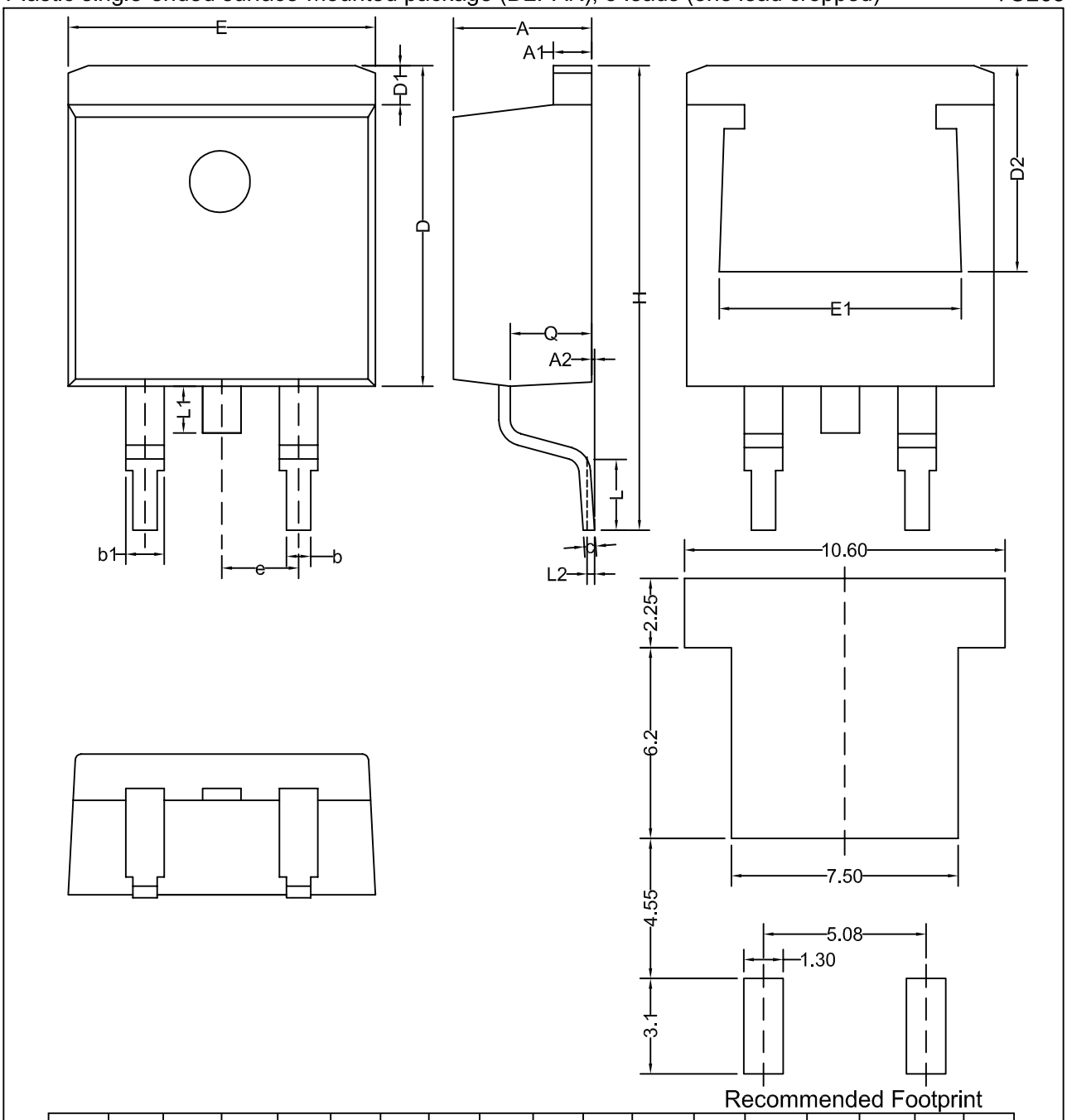


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) TO263



Unit	A	A1	A2	b	b1	c	D	D1	D2	e	E	E1	H	L	L1	L2	Q
min	4.10	1.22	0.00	0.60	1.05	0.34	---	1.20	6.60	2.54 (BSC)	9.70	7.80	14.80	2.10	---	0.25 (BSC)	2.20
max	4.70	1.40	0.25	0.90	1.45	0.64	11.00	1.60	---		10.30	---	15.80	2.90	1.75		2.79

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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13. Contents

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